74AHC1G126-Q100; 74AHCT1G126-Q100

Bus buffer/line driver; 3-state

Rev. 1 — 26 March 2013

Product data sheet

1. General description

74AHC1G126-Q100 and 74AHCT1G126-Q100 are high-speed Si-gate CMOS devices. They provide one non-inverting buffer/line driver with 3-state output. The output enable input pin (OE) controls the 3-state output. A LOW at pin OE causes the output to assume a high-impedance OFF-state.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)

3. Ordering information

Table 1. Ordering information

Type number	Package	Package									
	Temperature range	Name	Description	Version							
74AHC1G126GW-Q100	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package;	SOT353-1							
74AHCT1G126GW-Q100			5 leads; body width 1.25 mm								
74AHC1G126GV-Q100	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753							
74AHCT1G126GV-Q100											



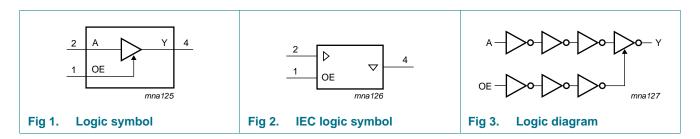
4. Marking

Table 2. Marking codes

Type number	Marking ^[1]
74AHC1G126GW-Q100	AN
74AHCT1G126GW-Q100	CN
74AHC1G126GV-Q100	A26
74AHCT1G126GV-Q100	C26

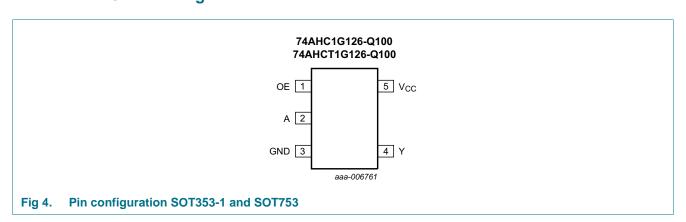
^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
OE	1	output enable input
Α	2	data input A
GND	3	ground (0 V)
Υ	4	data output Y
n.c.	-	not connected
V_{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state

Input	Output	
OE	A	Υ
Н	L	L
Н	Н	Н
L	X	Z

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					-
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_1 < -0.5 \text{ V}$	<u>[1]</u> –20	-	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	75	mA
I_{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	250	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] For TSSOP5 and SC-74A packages: above 87.5 $^{\circ}$ C the value of P_{tot} derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter Conditions			1G126-Q	100	74AHC	Unit		
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise	V_{CC} = 3.3 V \pm 0.3 V	-	-	100	-	-	-	ns/V
	and fall rate	V_{CC} = 5.0 V \pm 0.5 V	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C	;	–40 °C	to +85 °C	-40 °C 1	Unit	
			Min	Тур	Max	Min	Max	Min	Max	Ī
74AHC1	G126-Q100					1				
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
	V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V	
V_{IL}	L LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V_{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_{O} = -50 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \mu A; V_{CC} = 3.0 V$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_{O} = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_O = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.25	-	±2.5	-	±10	μΑ
I _I	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to 5.5 V}$	-	-	0.1	-	1.0	-	2.0	μА
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	2.0	-	20	-	40	μΑ

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Table 7. Static characteristics ...continued Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C	to +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
Cı	input capacitance		-	3	10	-	10	-	10	pF
74AHCT	1G126-Q100									
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	8.0	-	0.8	-	0.8	V
V _{OH} HIGH-level		$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -50 \ \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -8.0 \text{ mA}$	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	OL LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_O = 50 \mu A$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
I _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.25	-	±2.5	-	±10	μΑ
I _I	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	2.0	-	20	-	40	μΑ
Δl _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V};$ other inputs at V_{CC} or GND; $I_O = 0 \text{ A};$ $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
Cı	input capacitance		-	3	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics GND = 0 V; For test circuit see Figure 7.

Symbol	Parameter	Conditions		25 °C -4		-40 °C	-40 °C to +85 °C		-40 °C to +125 °C		
				Min	Тур	Max	Min	Max	Min	Max	
74AHC1	G126-Q100										
t _{pd} propagation	A to Y; see Figure 5	<u>[1]</u>									
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[2]								
		C _L = 15 pF		-	4.4	8.0	1.0	9.5	1.0	10.0	ns
		$C_L = 50 pF$		-	6.3	11.5	1.0	13.0	1.0	14.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C _L = 15 pF		-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		$C_{L} = 50 \text{ pF}$		-	4.7	7.5	1.0	8.5	1.0	9.5	ns

 Table 8.
 Dynamic characteristics ...continued

GND = 0 V; For test circuit see Figure 7.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C 1	to +125 °C	Uni
				Min	Тур	Max	Min	Max	Min	Max	
en	enable time	OE to Y; see Figure 6	<u>[1]</u>								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[2]								
		C _L = 15 pF		-	4.9	8.0	1.0	9.5	1.0	10.0	ns
		$C_L = 50 pF$		-	7.0	11.5	1.0	13.0	1.0	14.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		$C_{L} = 15 pF$		-	3.6	5.6	1.0	6.3	1.0	7.0	ns
		$C_L = 50 pF$		-	5.4	8.0	1.0	9.0	1.0	9.5	ns
dis	disable time	OE to Y; see Figure 6	<u>[1]</u>								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[2]								
		$C_{L} = 15 pF$		-	6.3	9.7	1.0	11.5	1.0	12.5	ns
		$C_L = 50 pF$		-	9.0	13.2	1.0	15.0	1.0	16.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		$C_{L} = 15 pF$		-	4.3	6.8	1.0	8.0	1.0	8.5	ns
		$C_L = 50 pF$		-	6.1	8.8	1.0	10.0	1.0	11.0	ns
C _{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}$; $f = 1 \text{ MHz}$; $V_I = \text{GND to } V_{CC}$	[4]	-	9	-	-	-	-	-	pF
74AHCT	1G126-Q100										
t _{pd}	propagation	A to Y; see Figure 5	<u>[1]</u>								
	delay	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C _L = 15 pF		-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF		-	4.7	7.5	1.0	8.5	1.0	9.5	ns
en	enable time	OE to Y; see Figure 6	<u>[1]</u>								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C _L = 15 pF		-	3.4	5.6	1.0	6.3	1.0	6.5	ns
		$C_L = 50 pF$		-	4.8	8.0	1.0	9.0	1.0	9.0	ns
dis	disable time	OE to Y; see Figure 6	<u>[1]</u>								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C _L = 15 pF			4.0	6.8	1.0	8.0	1.0	8.5	ns
		$C_{L} = 50 \text{ pF}$			5.7	8.8	1.0	10.0	1.0	11.5	ns

 Table 8.
 Dynamic characteristics ...continued

GND = 0 V; For test circuit see Figure 7.

Symbol	ymbol Parameter Conditions			25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit	
				Min	Тур	Max	Min	Max	Min	Max	
C_{PD}		per buffer; $C_L = 50 \text{ pF}$; $f = 1 \text{ MHz}$; $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	11	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
 - t_{en} is the same as t_{PZL} and t_{PZH} .
 - t_{dis} is the same as t_{PLZ} and t_{PHZ}.
- [2] Typical values are measured at $V_{CC} = 3.3 \text{ V}$.
- [3] Typical values are measured at $V_{CC} = 5.0 \text{ V}$.
- [4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i + \sum (C_L \times V_{CC}{}^2 \times f_o)$$
 where:

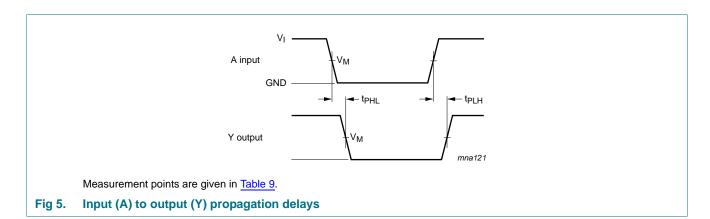
 f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in Volts.

12. Waveforms



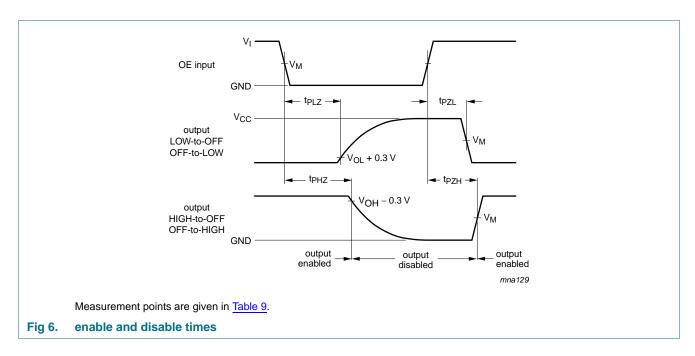
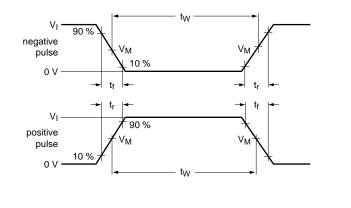
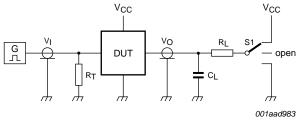


Table 9. Measurement points

Туре	Input	Output	
	V _M	V _I	V _M
74AHC1G126-Q100	$0.5 \times V_{CC}$	GND to V _{CC}	$0.5 \times V_{CC}$
74AHCT1G126-Q100	1.5 V	GND to 3.0 V	0.5 × V _{CC}





Test data is given in Table 10.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

 R_1 = Load resistance.

S1 = Test selection switch.

Fig 7. Test circuit for measuring switching times

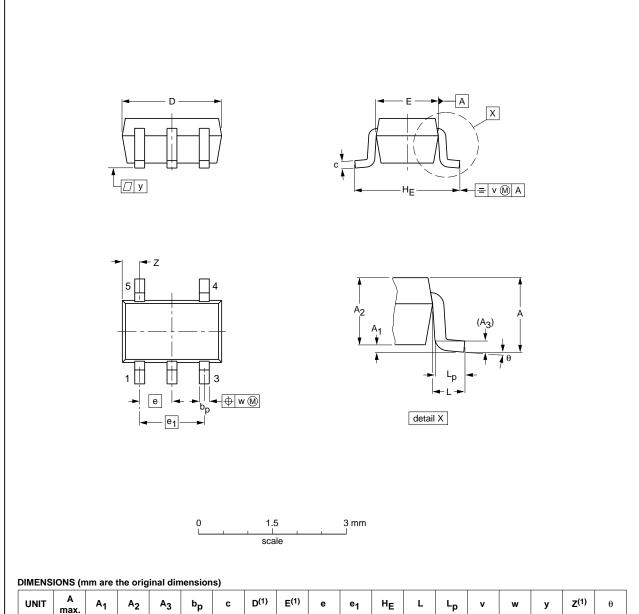
Table 10. Test data

Туре	Input		Load		S1 position			
	VI	t _r , t _f	C _L	R _L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
74AHC1G126-Q100	V_{CC}	≤ 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}	
74AHCT1G126-Q100	3 V	≤ 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}	

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UN	IIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	HE	L	Lp	v	w	у	Z ⁽¹⁾	θ
m	m	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT353-1		MO-203	SC-88A			-00-09-01 03-02-19	

Fig 8. Package outline SOT353-1 (TSSOP5)

74AHC_AHCT1G126_Q100

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SOT753

Plastic surface-mounted package; 5 leads В Α Χ = v M A 5 Q 3 detail X **→ w M** B

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	bp	С	D	E	е	HE	Lp	Q	v	w	у
mm	1.1 0.9	0.100 0.013		0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION		REFER	EUROPEAN	ISSUE DATE		
	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT753			SC-74A			-02-04-16 06-03-16

scale

Package outline SOT753 (SC-74A)

74AHC_AHCT1G126_Q100

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
MIL	Military
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC1G_AHCT1G126_Q100 v.1	20130326	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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